泰莱微波
Talent Microwave

Suzhou Talent Microwave,Inc
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Model:TLPA1G1.1G-50-57

Power Amplifier
1GHz-1.1GHz,Gain:50dB,Psat:57dBm

Feature:

- Wide Band: 1GHz-1.1GHz
- Gain: 45dB Min
- Psat Output Power: 57 dBm Min
- Good Power and Gain Flatness
- 50 Ohm Matched Input / Output

Electrical Specifications:

Parameter	Min	Typ	Max	Units
Frequency range		1-1.1		GHz
Gain	45	50		dB
Gain Flatness		±1	±2	dB
Output P1dB	50	53		dBm
Output Psat	57	57.5		dBm
Input VSWR		1.5	2	:1
DC Voltage	30	32	34	V DC
DC Supply Current		5	50	A
Impedance		50		Ohms

Mechanical Specifications:

Parameter	Value	Units
Input /Output Connector	SMA Female	
Bias	Solder Pin	
Size	230*150*25	mm
Weight	1500	g

Available 220V System Benchtop Amplifier

Absolute Maximum Ratings:

Parameter	Value
Supply Bias Voltage	30V
RF INPUT POWER	+5dBm
ESD sensitivity (HBm)	Class 0, passed 150V

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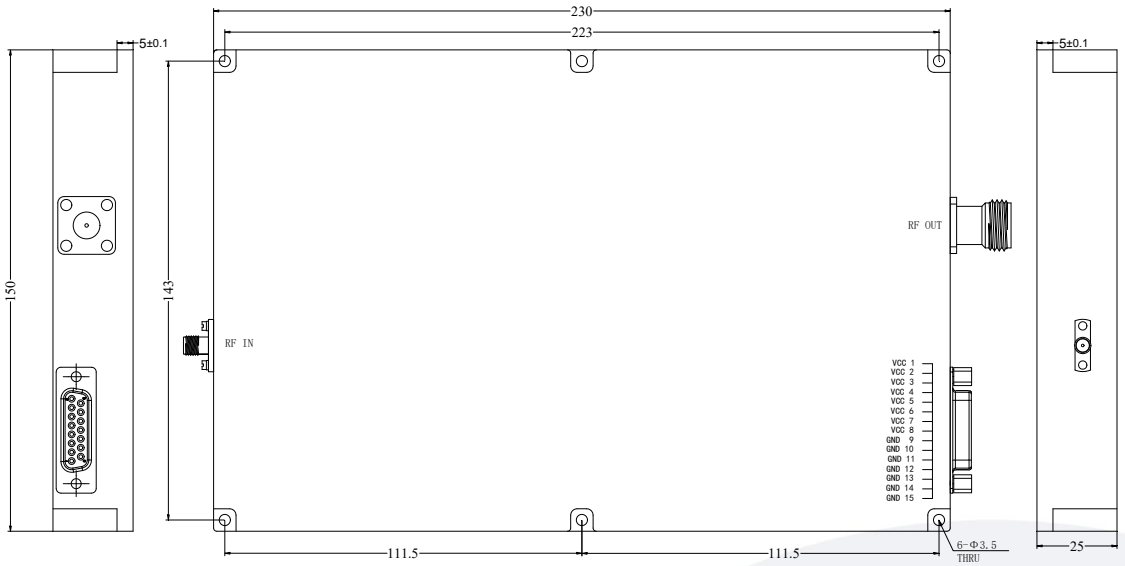
Outline Drawing:

Unit: mm



***Heat Sink Required During Operation

OBSERVE PRECAUTIONS
ELECTROSTATIC SENSITIVE
DEVICES

Environmental Conditions:

Parameter	Min	Typ	Max	Units
Operating Temperature	-45		+70	℃
Non-operating Temperature	-55		+125	℃
Relative humidity		95		%
Altitude	30,000			feet
Shock / Vibration(MIL-STD-810F)	25g rms (15 degree 2KHz) endurance, 1 hour per axis			
Shock(non operating)	20G for 11msc half sin wave,3 axis both directions			

Ordering Information:

Part Number	Description	Revision
TLPA1G1.1G-50-57	Power amplifier 1GHz-1.1GHz,Gain:50dB,Psat:57dBm,32V DC, Without Heatsink	Rev.1.0
TLPA1G1.1G-50-57-HS	Power amplifier 1GHz-1.1GHz,Gain:50dB,Psat:57dBm,32V DC, With Heatsink	Rev.1.0